

Features

- Bidirectional TVS 5 V
- ESD protection >30 kV
- Replacement for MLV (0402)
- Low Clamping Voltage
- Low Leakage Current

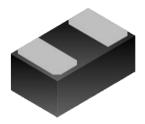
Applications

- Mother Board and Notebook, Cellular Phone,PDA, DV,Scanner and Set-Top Box etc.
- Suitable for Power Line , Low-speed data line interface

VTSB55AP3 ---- SURFACE MOUNT TVS Diodes

General Information

The VTSB55AP3 is designed with Vicsemi Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.



Absolute Maximum Ratings

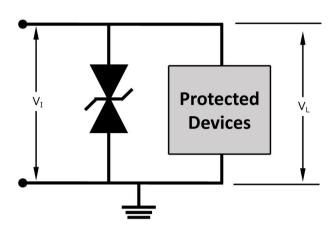
Parameter	Symbol	Value	Unit
Maximum Contact discharge voltage Per IEC61000-4-2		30KV	V
Maximum Air discharge voltage Per IEC61000-4-2		30KV	V
Maximum Operating temperature	T _{OPER}	-40 to +90	$^{\circ}$
Maximum Storage temperature	T_{STG}	-55 to +125	$^{\circ}$
Maximum lead temperature for soldering during 10s	T _L	260	င

Electrical Characteristics (@ T_A = 25 °C Unless Otherwise Noted)

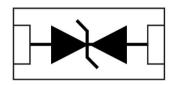
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Working Voltage	V_{RWM}	Any I/O pin to GND			5	V
Reverse Breakdown Voltage	V_{BR}	Any I/O pin to GND I_T =1mA	6			V
Positive Clamping Voltage	V_{C}	I_{pp} =20A, t_p =8/20 μ ; Any I/O pin to GND			15	V
Peak Pulse Current	I_{PP}	t _p =8/20μs waveform			20	Α
Reverse Leakage Current	I_{L}	V _{RWM} =5V ; Any I/O pin to GND			1.00	uA
Junction Capacitance	C _P	V _R =0V, f=1MHz; Any I/O pin to GND		30		pF



Typical Protection Circuit

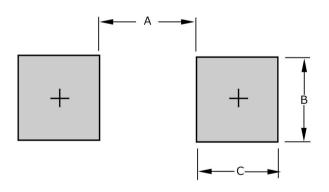


Block Diagram



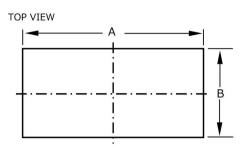
Bi-directional

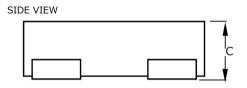
Recommended PCB Footprint

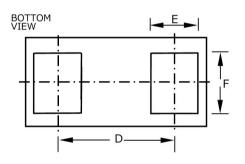


Dimension	DFN-2L
А	<u>0.30</u> (0.012)
В	<u>0.80</u> (0.031)
С	<u>0.55</u> (0.022)

Product Dimensions







Dimension	DFN-2L
А	<u>0.95-1.05</u> (0.037-0.041)
В	<u>0.55-0.65</u> (0.022-0.026)
С	<u>0.40-0.50</u> (0.016-0.020)
D	<u>0.65</u> (0.026)
Е	<u>0.10-0.35</u> (0.004-0.014)
F	<u>0.40-0.50</u> (0.016-0.020)

DIMENSIONS: MM (INCHES)



Performance Graphs

Figure 1: Peak Pulse Power Vs Pulse Time

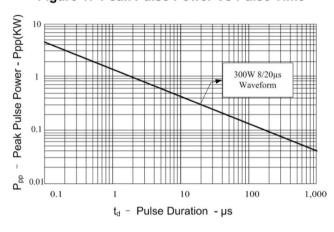


Figure 2: Power Derating Curve

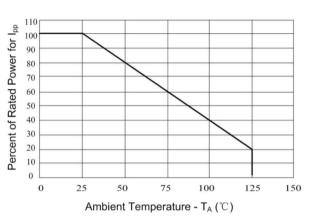


Figure 3: Clamping Voltage vs. Peak Pulse Current

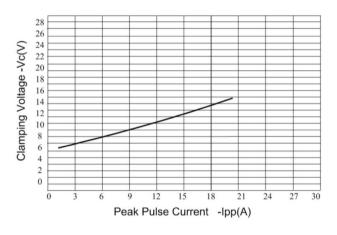


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

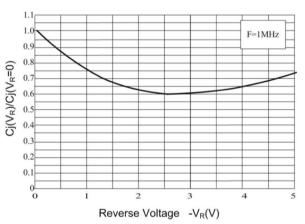


Figure 5: Pulse Waveform

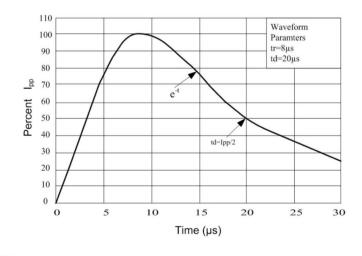
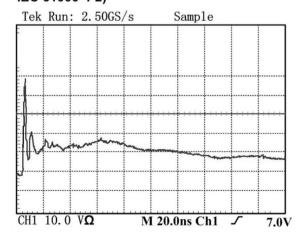


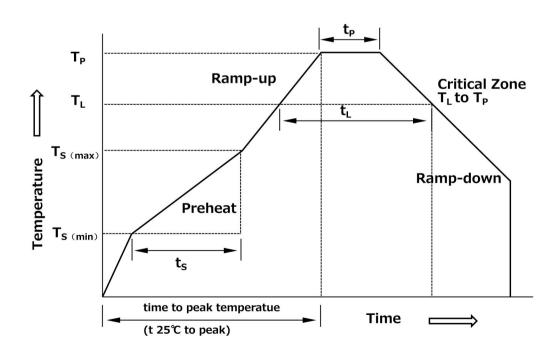
Figure 6: ESD Clamping(8kV Contact per IEC 61000-4-2)





Recommendable reflow soldering

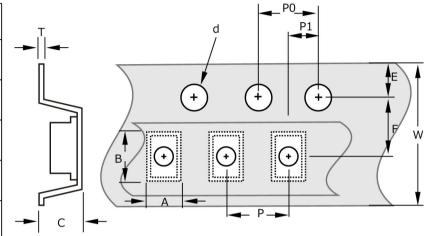
Profile Feature	Pb-Free Assembly	
Average Ramp-UP Rate	3 ℃/secondmax.	
(Tsmax to Tp)		
Preheat		
-Temperature Min(Tsmin)	150 ℃	
-Temperature Max(Tsmax)	200 ℃	
-Time(Tsmin to Tsmax)	60-180seconds	
Time maintained above:		
-Temperature(TL)	217 ℃	
-Time(tL)	60-150 seconds	
Peak/Classification Temperature(Tp)	260℃	
Time within 5℃ofactualPeak	20. 40 seconds	
Temperature(tp)	20-40 seconds	
Ramp-Down Rate	6℃/secondmax.	
Time 25℃toPeakTemperature	8 minutes max.	

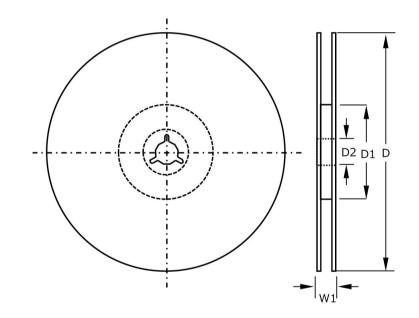




Packaging Information

Symbol	DFN-2L
А	0.7±0.05 (0.028±0.002)
В	1.15±0.05 (0.045±0.002)
С	0.47±0.05 (0.019±0.002)
d	1.55±0.05 (0.061±0.002)
D	180.00±2.00 (7.087±0.079)
D1	60.0±1.00 (2.362±0.039)
D2	<u>13.0±0.20</u> (0.516±0.008)
E	1.75±0.10 (0.069±0.004)
F	3.50±0.05 (0.138±0.002)
Р	2.00±0.10 (0.079±0.004)
P0	4.00±0.10 (0.157±0.004)
P1	2.00±0.05 (0.079±0.002)
Т	0.20±0.05 (0.008±0.002)
W	8.00±0.10 (0.315±0.004)
W1	11.6±1.00 (0.457±0.039)





DIMENSIONS: MM (INCHES)

Quantity of products in the taping package

- (1) Standard quantity: 5000 pcs/reel or 10000 pcs/Reel for the Series.
- (2) Shipping quantity is a multiple of standard quantity.
- (3) For additional information, please contact your local Sales Representative.